
Poster Presentation

[AMDp1]Oxide TFTs

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

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[AMDp1-5]Transfer Characteristics of H_2O_2 -Doped ZrInZnO Thin Film Transistors

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Solution-processed zirconium-indium-zinc-oxide thin-film transistors (ZIZO TFTs) were fabricated with and without hydrogen peroxide (H_2O_2). With an incorporation of H_2O_2 into the channel layer, threshold voltage shift under positive bias stress were improved. We realized the reduced trap density of ZIZO TFTs with 2 M H_2O_2 incorporation.